



Attorney's Docket No. 015290-506

Patent

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)
Ting CHIEN et al.) Group Art Unit: 1765
Application No.: 09/820,692) Examiner: K.C. Chen
Filed: March 30, 2001) Confirmation No. 5245
For: PLASMA ETCHING OF DIELECTRIC)
LAYER WITH SELECTIVITY TO STOP)
LAYER)

AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Reconsideration of the Official Action dated April 10, 2002 is respectfully
requested.

IN THE CLAIMS

A marked-up version of the claims showing insertions and deletions appears in
Appendix A. Please rewrite Claims 1-3 and 19, and add new Claims 21-22 as follows:

1. (Amended) A method of etching a dielectric layer with selectivity to an
underlying stop layer, comprising:

supporting a semiconductor substrate in a plasma etch reactor, the substrate
including a dielectric layer over a stop layer;

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